

**FEATURES**

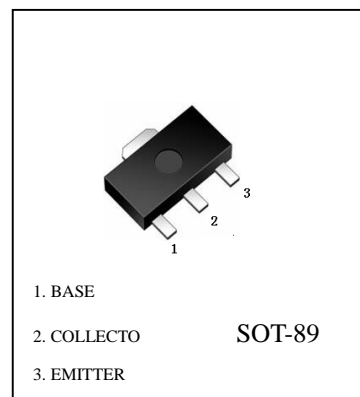
Complimentary to PXT8550

Collector current:  $I_C=1.5A$

MARKING: Y1



**PXT8050 (NPN)**



**MAXIMUM RATINGS (TA=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current -Continuous	$I_C$	1500	mA
Collector Power Dissipation	$P_C$	1000	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55-150	°C

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=20V, I_B=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	85		400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=800mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800mA, I_B=80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800mA, I_B=80mA$			1.2	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=1V, I_C=10mA$			1	V
Base-emitter positive forward voltage	$V_{BEF}$	$I_B=1A$			1.5	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=50mA, f=30MHz$	100			MHz
output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$			15	pF

**CLASSIFICATION OF HFE**

Rank	B	C	D	D1
Range	85-160	120-200	160-300	300-400

**PXT8050** Typical Characteristics

